

# **TIS73 TIS74**



# **N-Channel General Purpose Amplifier**

This device is designed for low level analog switching, sample and hold circuits and chopper stabalized amplifiers. Sourced from Process 54.

## **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{DG}$	Drain-Gate Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	- 30	V
I <sub>GF</sub>	Forward Gate Current	10	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		TIS73 / TIS74	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# N-Channel General Purpose Amplifier (continued)

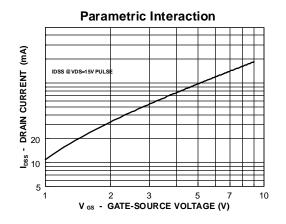
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V <sub>(BR)GSS</sub>	Gate-Source Breakdown Voltage	$I_G = 1.0 \mu\text{A}, V_{DS} = 0$	- 30		V
I <sub>GSS</sub>	Gate Reverse Current	V <sub>GS</sub> = 15 V, V <sub>DS</sub> = 0 V <sub>GS</sub> = 15 V, V <sub>DS</sub> = 0, T <sub>A</sub> = 100°C		- 2.0 - 5.0	nA μA
$I_{D(Off)}$	Drain Cutoff Leakage Current	$V_{DS} = 15 \text{ V}, V_{GS} = 9, T_{A} = 100 \text{ C}$ $V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, T_{A} = 100 \text{ C}$		- 2.0 - 5.0	nA μA
V <sub>GS(off)</sub>	Gate-Source Cutoff Voltage	$V_{DS} = 15 \text{ V}, V_{GS} = 16 \text{ V}, V_{A} = 180 \text{ G}$ $V_{DS} = 15 \text{ V}, I_{D} = 4.0 \text{ nA}$ TIS73 TIS74	- 4.0 - 2.0	- 10 - 6.0	V
ON CHAF	RACTERISTICS  Zero-Gate Voltage Drain Current*	$V_{DS} = 15 \text{ V}, V_{GS} = 0$	50		mA
		$V_{pq} = 15 \text{ V}, V_{qq} = 0$	50		mA
			20	100	mA
r <sub>DS(on)</sub>	Drain-Source On Resistance	$V_{DS} \le 0.1 \text{ V}, V_{GS} = 0,$ TIS73 f = 1.0 kHz TIS74		25 40	$\Omega$
SMALL-S	IGNAL CHARACTERISTICS Input Capacitance	V <sub>DS</sub> = 0, V <sub>GS</sub> = 10 V, f = 1.0 MHz		18	pF
				0.0	,
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>DS</sub> = 0, V <sub>GS</sub> = 10 V, f = 1.0 MHz		8.0	pF
SWITCHI	NG CHARACTERISTICS				
t <sub>r</sub>	Rise Time	$V_{GS(off)} = 10 \text{ mA}, V_{GS(on)} = 0,$ $I_D = 20 \text{ mA}, V_{DS} = 10 \text{ V}$ TIS73 TIS74		3.0 4.0	ns ns
ton	Turn-On Time	$V_{GS(off)} = 10 \text{ mA}, V_{GS(on)} = 0,$ $I_D = 20 \text{ mA}, V_{DS} = 10 \text{ V}$		6.0	ns
toff	Turn-Off Time	$V_{GS(Off)} = 10 \text{ mA}, V_{GS(On)} = 0,$		25	

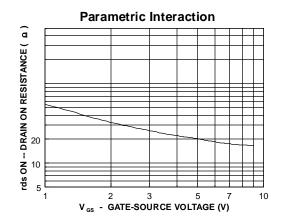
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  3.0%

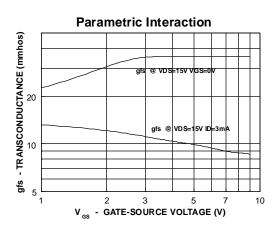
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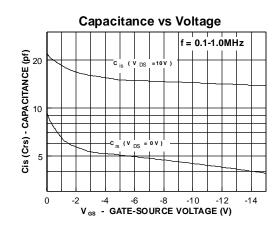
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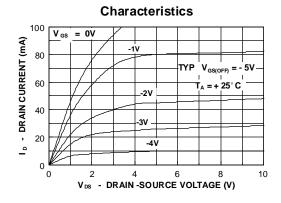
# **Typical Characteristics**



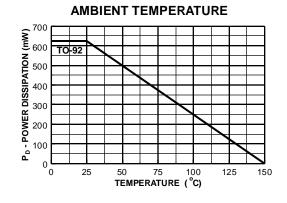








**Common Drain-Source** 



**POWER DISSIPATION vs** 

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